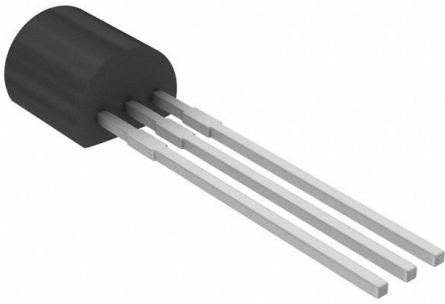


# BC369,112 Datasheet

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<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	BC369,112-DG
Manufacturer	<a href="#">NXP USA Inc.</a>
Manufacturer Product Number	BC369,112
Description	TRANS PNP 20V 1A TO92-3
Detailed Description	Bipolar (BJT) Transistor PNP 20 V 1 A 140MHz 830 mW Through Hole TO-92-3



Tel: +00 852-30501935

RFQ Email: [Info@DiGi-Electronics.com](mailto:Info@DiGi-Electronics.com)

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## Purchase and inquiry

Manufacturer Product Number:

BC369,112

Series:

-

Transistor Type:

PNP

Voltage - Collector Emitter Breakdown (Max):

20 V

Current - Collector Cutoff (Max):

100nA (ICBO)

Power - Max:

830 mW

Operating Temperature:

150°C (TJ)

Package / Case:

TO-226-3, TO-92-3 (TO-226AA) Formed Leads

Base Product Number:

BC36

Manufacturer:

NXP USA Inc.

Product Status:

Obsolete

Current - Collector (Ic) (Max):

1 A

Vce Saturation (Max) @ Ib, Ic:

500mV @ 100mA, 1A

DC Current Gain (hFE) (Min) @ Ic, Vce:

85 @ 500mA, 1V

Frequency - Transition:

140MHz

Mounting Type:

Through Hole

Supplier Device Package:

TO-92-3

## Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.21.0075

Moisture Sensitivity Level (MSL):

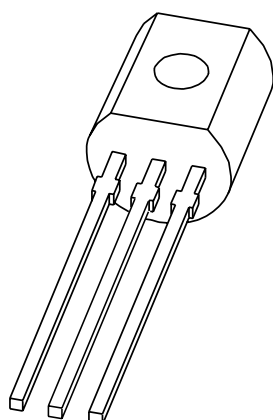
1 (Unlimited)

ECCN:

EAR99

**DISCRETE SEMICONDUCTORS**

# DATA SHEET



**BC369**

**PNP medium power transistor;  
20 V, 1 A**

Product data sheet  
Supersedes data of 2003 Nov 20

2004 Nov 05

## PNP medium power transistor; 20 V, 1 A

## BC369

### FEATURES

- High current
- Two current gain selections.

### APPLICATIONS

- Linear voltage regulators
- High side switches
- Supply line switches
- MOSFET drivers
- Audio pre-amplifiers.

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	–	–20	V
$I_C$	collector current (DC)	–	–1	A
$I_{CM}$	peak collector current	–	–2	A
$h_{FE}$	DC current gain			
	BC369	85	375	
	BC369-16	100	250	
	BC369-25	160	375	

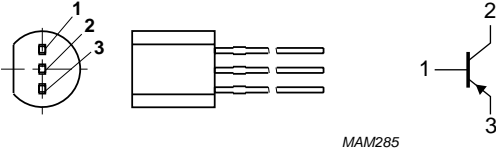
### DESCRIPTION

PNP medium power transistor (see “Simplified outline, symbol and pinning”) for package details.

### PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE
	PHILIPS	EIAJ	
BC369	SOT54	SC-43A	C369
BC369-16	SOT54	SC-43A	C36916
BC369-25	SOT54	SC-43A	C36925

### SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING	
		PIN	DESCRIPTION
BC369		1 2 3	base collector emitter

### ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BC369	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54
BC369-16			
BC369-25			

# PNP medium power transistor; 20 V, 1 A

BC369

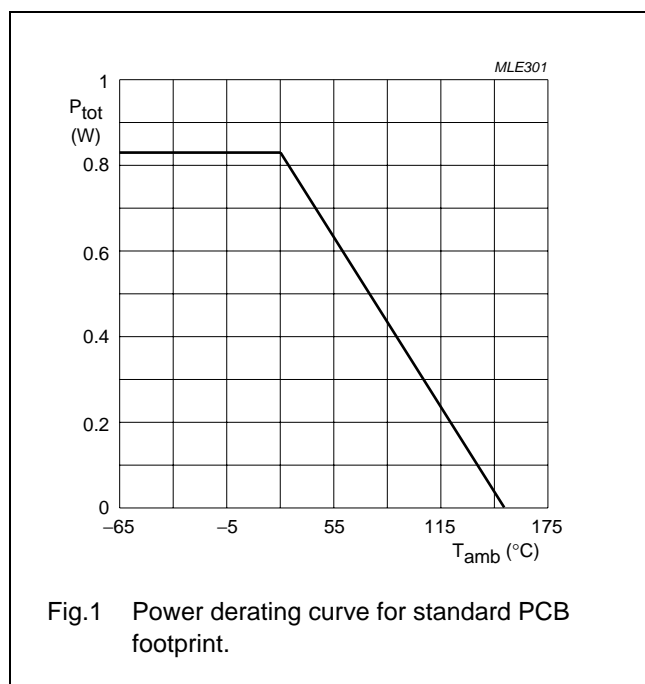
## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	–32	V
$V_{CEO}$	collector-emitter voltage	open base	–	–20	V
$V_{EBO}$	emitter-base voltage	open collector	–	–5	V
$I_C$	collector current (DC)		–	–1	A
$I_{CM}$	peak collector current		–	–2	A
$I_{BM}$	peak base current		–	–200	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$ ; notes 1 and 2	–	830	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C
$T_{amb}$	ambient temperature		–65	+150	°C

## Notes

1. Refer to SOT54 (SC-43A) standard mounting conditions.
2. Device mounted on a FR4 printed-circuit board; single-sided copper; tin-plated; standard footprint for SOT54.



PNP medium power transistor;  
20 V, 1 A

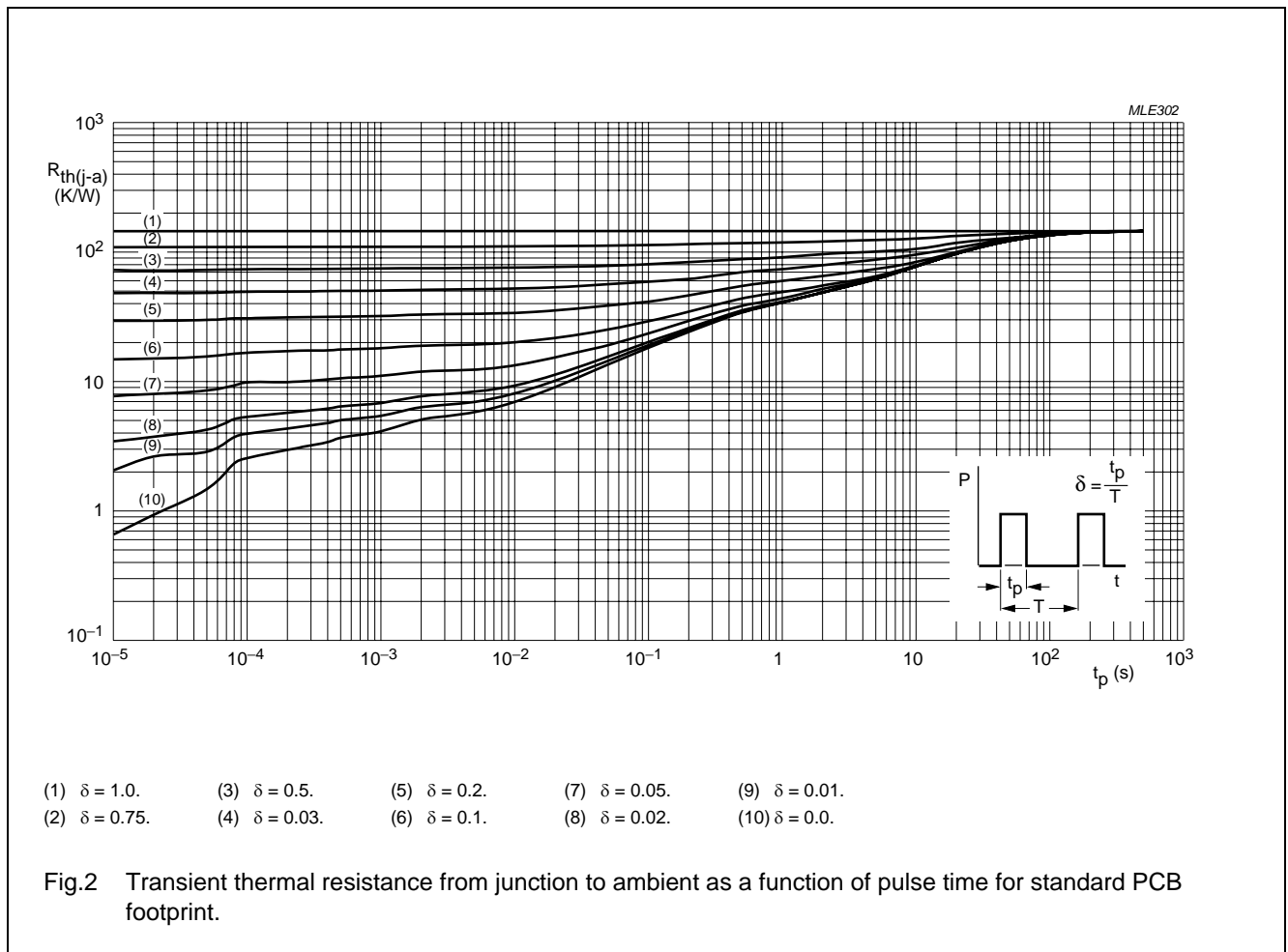
BC369

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$ ; notes 1 and 2	150	K/W

#### Notes

1. Refer to SOT54 (SC-43A) standard mounting conditions.
2. Device mounted on a FR4 printed-circuit board; single-sided copper; tin-plated; standard footprint for SOT54.



PNP medium power transistor;  
20 V, 1 A

BC369

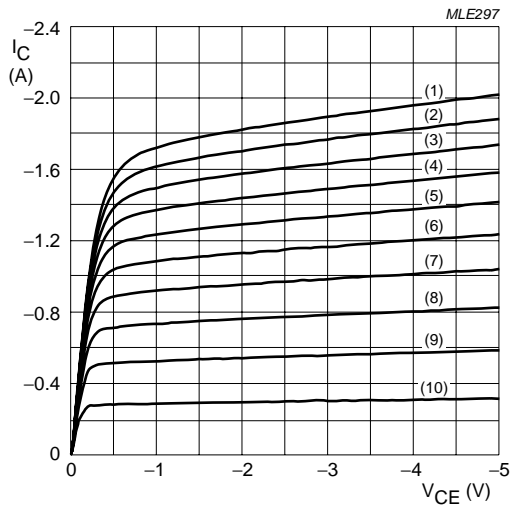
**CHARACTERISTICS**

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector-base cut-off current	$V_{CB} = -25\text{ V}; I_E = 0\text{ A}$	–	–	–100	nA
		$V_{CB} = -25\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ °C}$	–	–	–10	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0\text{ A}$	–	–	–100	nA
$h_{FE}$	DC current gain BC369	$V_{CE} = -10\text{ V}; I_C = -5\text{ mA}$	50	–	–	
		$V_{CE} = -1\text{ V}; I_C = -500\text{ mA}$	85	–	375	
	BC369-16 BC369-25	$V_{CE} = -1\text{ V}; I_C = -1\text{ A}$	60	–	–	
		$V_{CE} = -1\text{ V}; I_C = -500\text{ mA}$	100	–	250	
		$V_{CE} = -1\text{ V}; I_C = -500\text{ mA}$	160	–	375	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -1\text{ A}; I_B = -100\text{ mA}$	–	–	–500	mV
$V_{BE}$	base-emitter voltage	$V_{CE} = -10\text{ V}; I_C = -5\text{ mA}$	–	–	–700	mV
		$V_{CE} = -1\text{ V}; I_C = -1\text{ A}$	–	–	–1	V
$C_c$	collector capacitance	$V_{CB} = -10\text{ V}; I_E = i_e = 0\text{ A}; f = 1\text{ MHz}$	–	28	–	pF
$f_T$	transition frequency	$V_{CE} = -5\text{ V}; I_C = -50\text{ mA}; f = 100\text{ MHz}$	40	140	–	MHz

# PNP medium power transistor; 20 V, 1 A

BC369

**BC369-16.** $T_{amb} = 25\text{ }^{\circ}\text{C}.$ 

(1) $I_B = -18\text{ mA}.$	(6) $I_B = -9.0\text{ mA}.$
(2) $I_B = -16.2\text{ mA}.$	(7) $I_B = -7.2\text{ mA}.$
(3) $I_B = -14.4\text{ mA}.$	(8) $I_B = -5.4\text{ mA}.$
(4) $I_B = -12.6\text{ mA}.$	(9) $I_B = -3.6\text{ mA}.$
(5) $I_B = -10.8\text{ mA}.$	(10) $I_B = -1.8\text{ mA}.$

Fig.3 Collector current as a function of collector-emitter voltage; typical values.

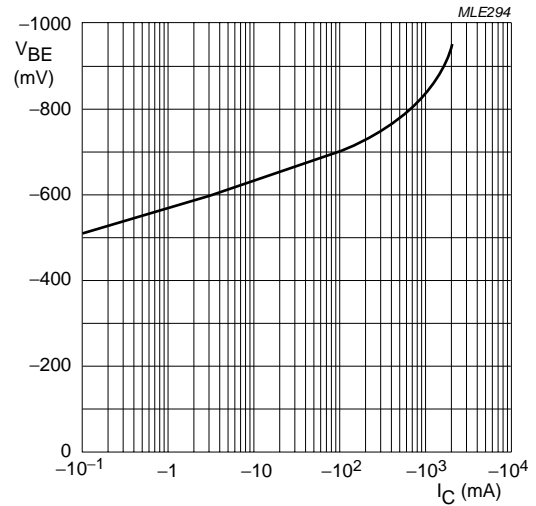
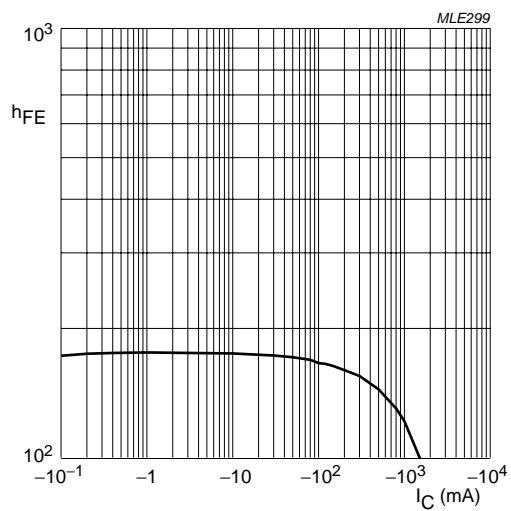
**BC369-16.** $V_{CE} = -1\text{ V}.$ 

Fig.4 Base-emitter voltage as a function of collector current; typical values.



PNP medium power transistor;  
20 V, 1 A

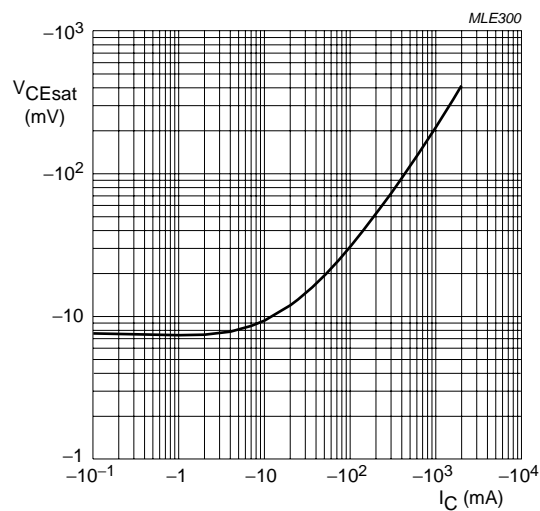
BC369



BC369-16.

 $V_{CE} = -1$  V.

Fig.5 DC current gain as a function of collector current; typical values.



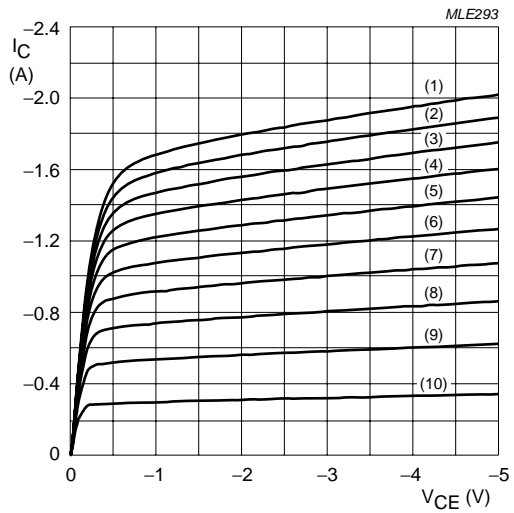
BC369-16.

 $I_C/I_B = 10$ .

Fig.6 Collector-emitter saturation voltage as a function of collector current; typical values.

# PNP medium power transistor; 20 V, 1 A

BC369

**BC369-25.** $T_{amb} = 25\text{ }^{\circ}\text{C}.$ 

- |                              |                              |
|------------------------------|------------------------------|
| (1) $I_B = -12\text{ mA}.$   | (6) $I_B = -6.0\text{ mA}.$  |
| (2) $I_B = -10.8\text{ mA}.$ | (7) $I_B = -4.8\text{ mA}.$  |
| (3) $I_B = -9.6\text{ mA}.$  | (8) $I_B = -3.6\text{ mA}.$  |
| (4) $I_B = -8.4\text{ mA}.$  | (9) $I_B = -2.4\text{ mA}.$  |
| (5) $I_B = -7.2\text{ mA}.$  | (10) $I_B = -1.2\text{ mA}.$ |

Fig.7 Collector current as a function of collector-emitter voltage; typical values.

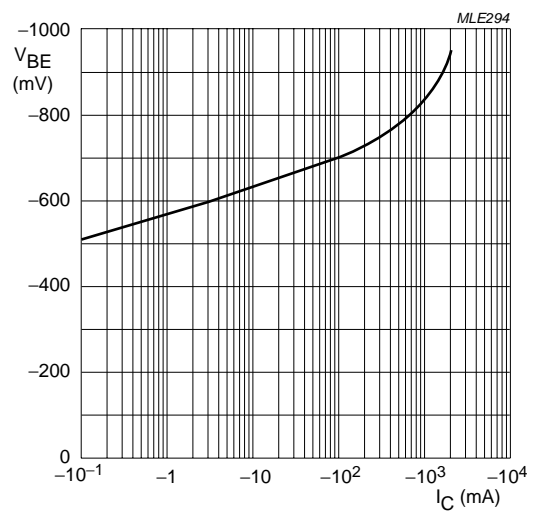
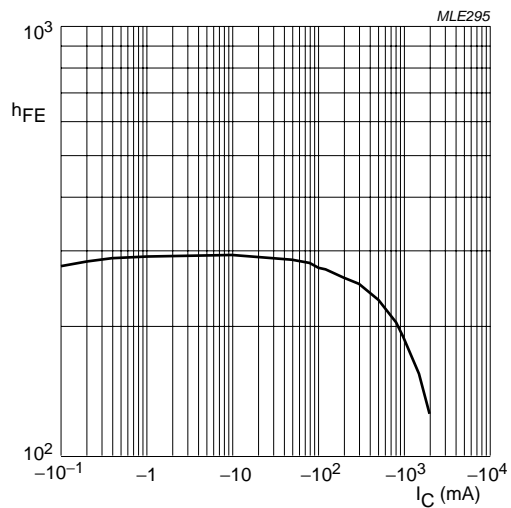
**BC369-25.** $V_{CE} = -1\text{ V}.$ 

Fig.8 Base-emitter voltage as a function of collector current; typical values.

PNP medium power transistor;  
20 V, 1 A

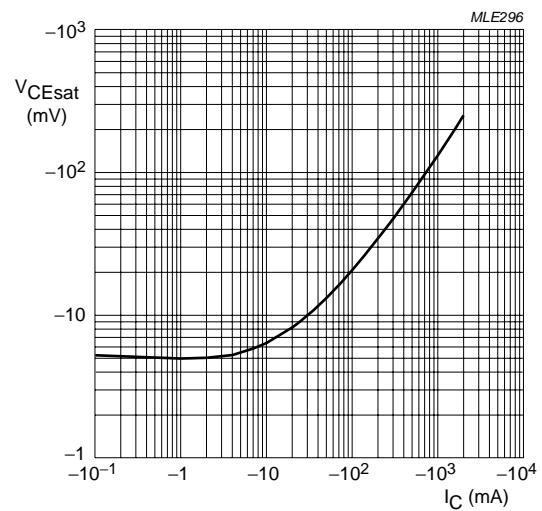
BC369



**BC369-25.**

$V_{CE} = -1$  V.

Fig.9 DC current gain as a function of collector current; typical values.



**BC369-25.**

$I_C/I_B = 10$ .

Fig.10 Collector-emitter saturation voltage as a function of collector current; typical values.

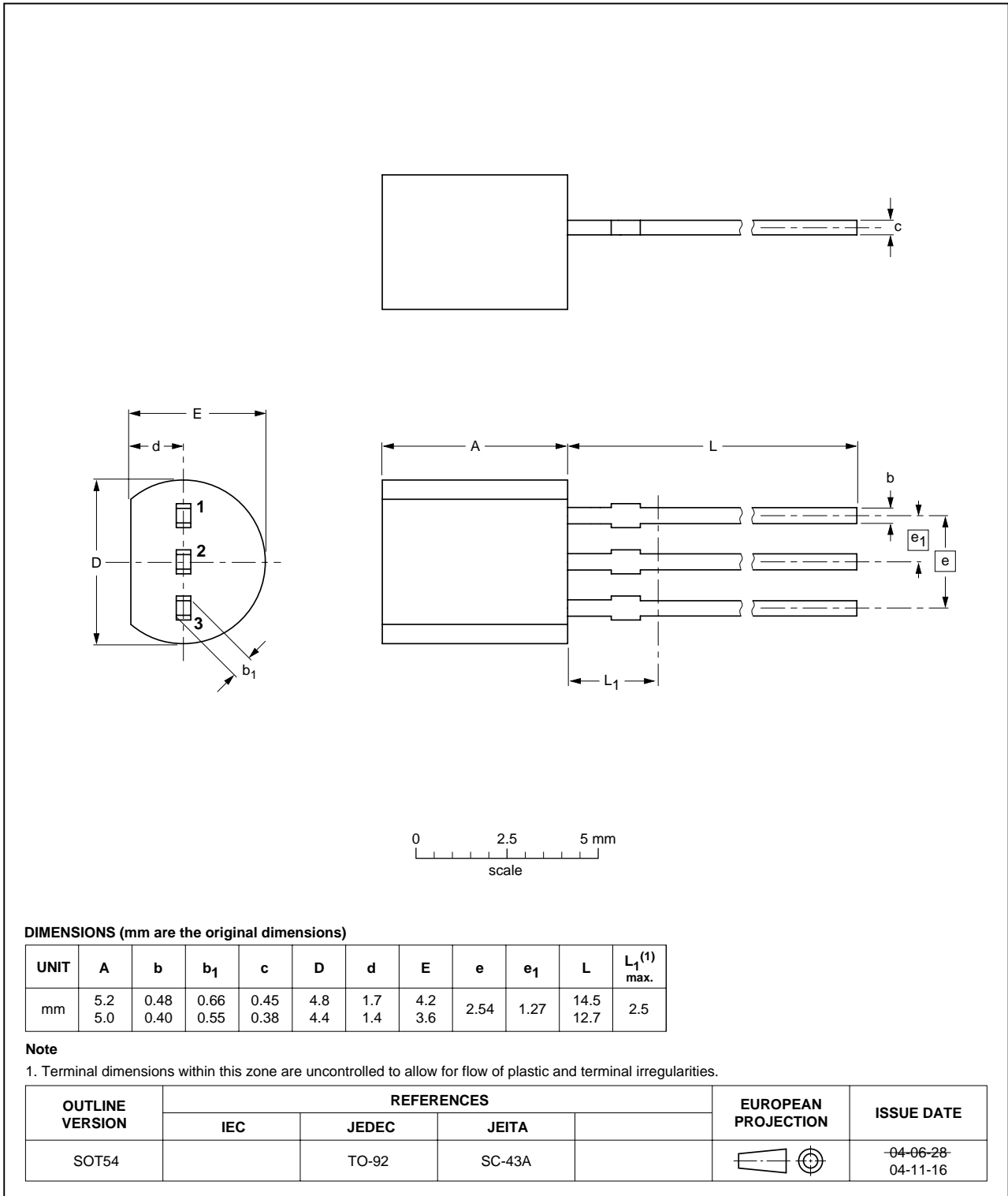
PNP medium power transistor;  
20 V, 1 A

BC369

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



# PNP medium power transistor; 20 V, 1 A

BC369

## DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

## Notes

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# ***NXP Semiconductors***

## **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

## **Contact information**

For additional information please visit: <http://www.nxp.com>

For sales offices addresses send e-mail to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

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